

MOCD213M

Dual Channel Phototransistor Small Outline Surface Mount Optocouplers

Features

- U.L. recognized (File #E90700, Volume 2)
- VDE recognized (File #136616) (add option "V" for VDE approval, i.e. MOCD213VM)
- Dual channel coupler
- Convenient plastic SOIC-8 surface mountable package style
- Minimum current transfer ratio 100% with input current of 10mA
- Minimum BV_{CEO} of 70 Volts guaranteed
- Standard SOIC-8 footprint, with 0.050" lead spacing
- Compatible with dual wave, vapor phase and IR reflow soldering
- High input-output isolation of 2500 $V_{AC(rms)}$ guaranteed

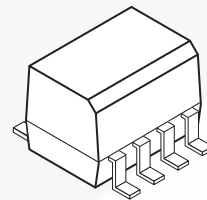
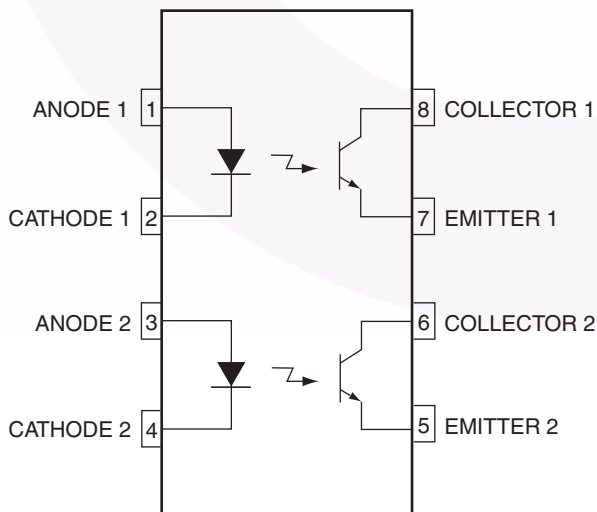
Description

The MOCD213M device consists of two gallium arsenide infrared emitting diodes optically coupled to two monolithic silicon phototransistor detectors, in a surface mountable, small outline plastic package. It is ideally suited for high density applications and eliminates the need for through-the-board mounting.

Applications

- Feedback control circuits
- Interfacing and coupling systems of different potentials and impedances
- General purpose switching circuits
- Monitor and detection circuits

Schematic



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ Unless otherwise specified)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Rating	Value	Unit
EMITTER			
I_F	Forward Current – Continuous	60	mA
I_F (pk)	Forward Current – Peak (PW = 100 μ s, 120 pps)	1.0	A
V_R	Reverse Voltage	6.0	V
P_D	LED Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	90	mW
		0.8	mW/ $^\circ\text{C}$
DETECTOR			
V_{CEO}	Collector-Emitter Voltage	70	V
V_{ECO}	Emitter-Base Voltage	7.0	V
I_C	Collector Current-Continuous	150	mA
P_D	Detector Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	150	mW
		1.76	mW/ $^\circ\text{C}$
TOTAL DEVICE			
V_{ISO}	Input-Output Isolation Voltage (f = 60Hz, t = 1 min.)	2500	Vac(rms)
P_D	Total Device Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	250	mW
		2.94	mW/ $^\circ\text{C}$
T_A	Ambient Operating Temperature Range	-40 to +100	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-40 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.*	Max.	Unit
EMITTER						
V_F	Input Forward Voltage	$I_F = 30\text{mA}$		1.25	1.55	V
I_R	Reverse Leakage Current	$V_R = 6.0\text{V}$		0.001	100	μA
C	Capacitance			18		pF
DETECTOR						
I_{CEO1}	Collector-Emitter Dark Current	$V_{CE} = 10\text{V}, T_A = 25^\circ\text{C}$		1.0	50	nA
I_{CEO2}		$V_{CE} = 10\text{V}, T_A = 100^\circ\text{C}$		1.0		μA
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 100\mu\text{A}$	70	120		V
BV_{ECO}	Emitter-Collector Breakdown Voltage	$I_E = 100\mu\text{A}$	7.0	7.8		V
C_{CE}	Collector-Emitter Capacitance	$f = 1.0\text{MHz}, V_{CE} = 0\text{V}$		7.0		pF
COUPLED						
CTR	Current Transfer Ratio ⁽⁴⁾	$I_F = 10\text{mA}, V_{CE} = 10\text{V}$	100			%
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 2.0\text{mA}, I_F = 10\text{mA}$		0.15	0.4	V
t_{on}	Turn-On Time	$I_C = 2.0\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$ (Fig. 6)		3.0		μs
t_{off}	Turn-Off Time	$I_C = 2.0\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$ (Fig. 6)		2.8		μs
t_r	Rise Time	$I_C = 2.0\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$ (Fig. 6)		1.6		μs
t_f	Fall Time	$I_C = 2.0\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$ (Fig. 6)		2.2		μs
V_{ISO}	Isolation Surge Voltage ⁽¹⁾⁽²⁾⁽³⁾	$f = 60\text{Hz}, t = 1\text{min.}$	2500			Vac(rms)
R_{ISO}	Isolation Resistance ⁽²⁾	$V_{I-O} = 500\text{V}$	10^{11}			Ω
C_{ISO}	Isolation Capacitance ⁽²⁾	$V_{I-O} = 0\text{V}, f = 1\text{MHz}$		0.2		pF

*Typical values at $T_A = 25^\circ\text{C}$ **Notes:**

1. Input-Output Isolation Voltage, V_{ISO} , is an internal device dielectric breakdown rating.
2. For this test, Pins 1, 2, 3 and 4 are common and Pins 5, 6, 7 and 8 are common.
3. V_{ISO} rating of 2500 $V_{AC(rms)}$ for $t = 1\text{min.}$ is equivalent to a rating of 3,000 $V_{AC(rms)}$ for $t = 1\text{sec.}$
4. Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.

Typical Performance Curves

Fig. 1 LED Forward Voltage vs. Forward Current

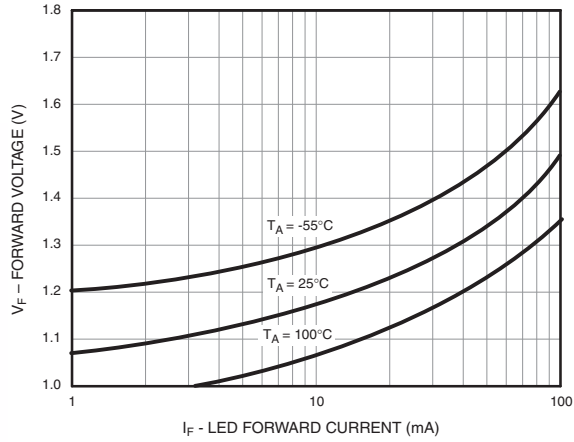


Fig. 2 Output Current vs. Input Current

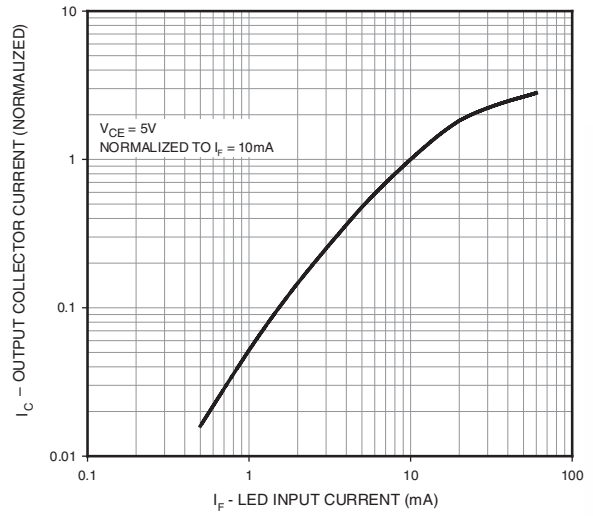


Fig. 3 Output Current vs. Ambient Temperature

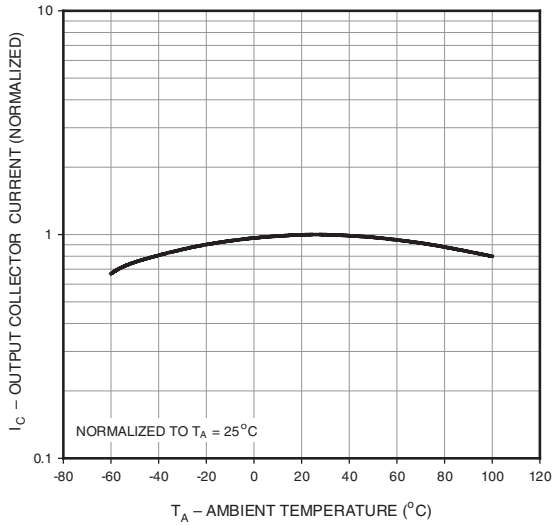


Fig. 4 Output Current vs. Collector - Emitter Voltage

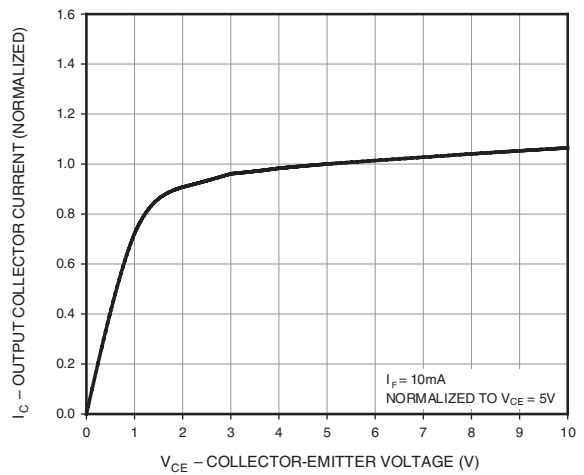
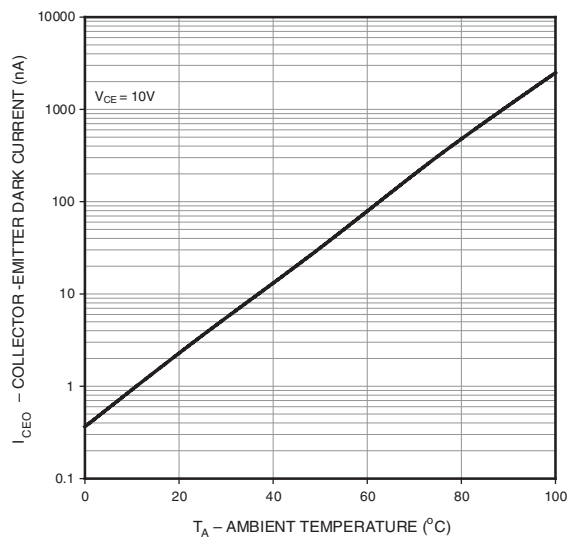


Fig. 5 Dark Current vs. Ambient Temperature



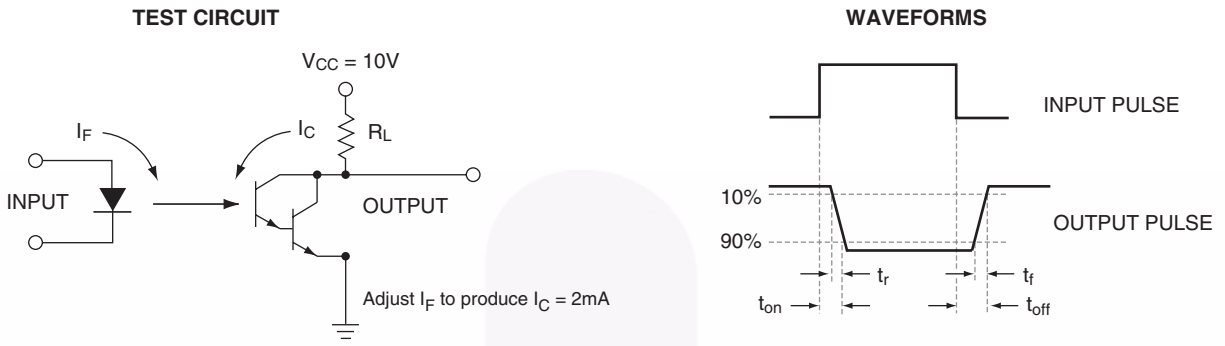


Figure 6. Switching Time Test Circuit and Waveform

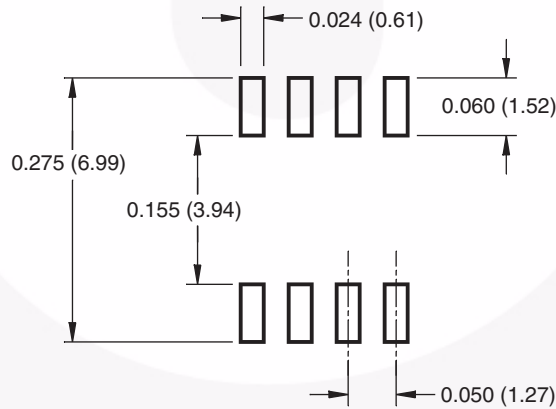


Package Dimensions

8-pin SOIC Surface Mount



Recommended Pad Layout



Dimensions in inches (mm).

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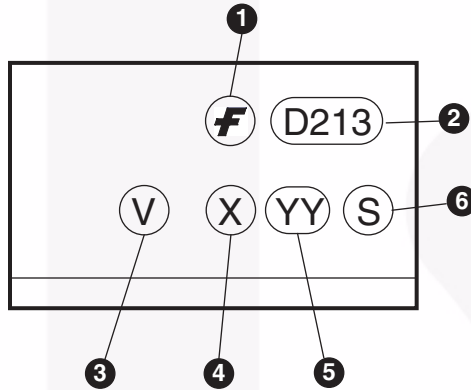
Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

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Ordering Information

Option	Order Entry Identifier	Description
V	V	VDE 0884
R2	R2	Tape and reel (2500 units per reel)
R2V	R2V	VDE 0884, Tape and reel (2500 units per reel)

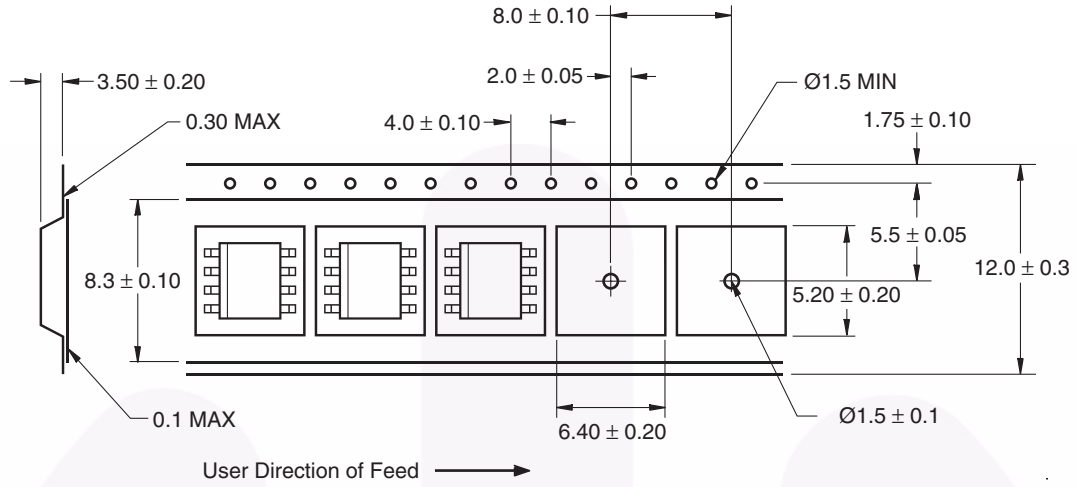
Marking Information



Definitions

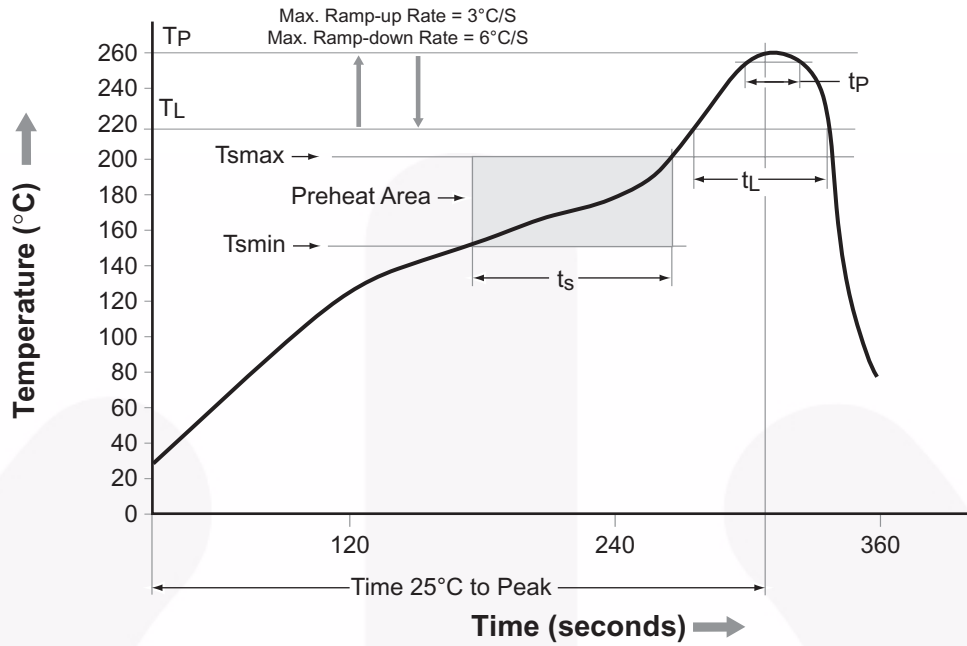
1	Fairchild logo
2	Device number
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)
4	One digit year code, e.g., '8'
5	Two digit work week ranging from '01' to '53'
6	Assembly package code

Carrier Tape Specifications



Dimensions in mm

Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmín)	150°C
Temperature Max. (Tsmáx)	200°C
Time (ts) from (Tsmín to Tsmáx)	60–120 seconds
Ramp-up Rate (tL to tP)	3°C/second max.
Liquidous Temperature (TL)	217°C
Time (tL) Maintained Above (TL)	60–150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (tp) within 5°C of 260°C	30 seconds
Ramp-down Rate (TP to TL)	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.



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